

Abstracts

GaAs FET Limiting Amplifier Designed for Low AM to PM Conversion

C.R. Baughman and J.Y. Chin. "GaAs FET Limiting Amplifier Designed for Low AM to PM Conversion." 1982 MTT-S International Microwave Symposium Digest 82.1 (1982 [MWSYM]): 268-270.

A 0.5 μm gate length GaAs FET has been characterized for use in a low AM to PM conversion limiting amplifier at 12.0 GHz. A unique linear behavior for FET AM/PM is observed with respect to DC biasing, and its data are presented along with input and output matching information. FET limiting amplifier design techniques and data on a nine-stage amplifier are also reported.

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